

0.8 μm SLD CAN AS8K215GY30M

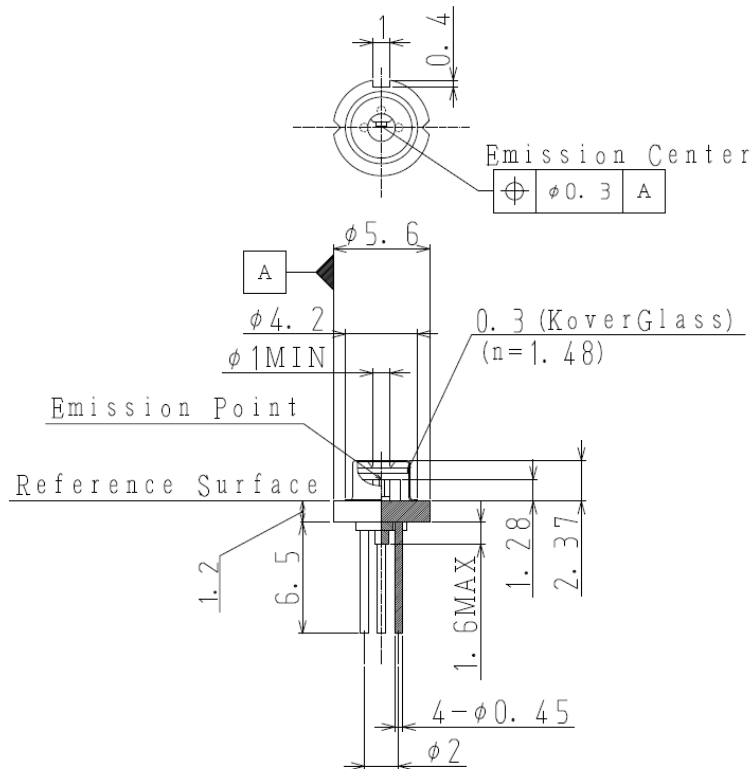
AS8K215GY30M is SLD (Super-Luminescent Diode) developed as incoherent light sources for various optical measurements including Optical Coherent Tomography (OCT). The device emits high-intensity and wide spectral incoherent light. The narrow radiation angle enables high-efficient optical coupling to a single mode fiber.

FEATURES

- Optical Output Power : 5 mW
- Spectral Bandwidth : 15 nm typ.
- $\Phi 5.6$ CAN package
- Built-in monitor photo diode

APPLICATIONS

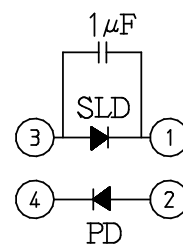
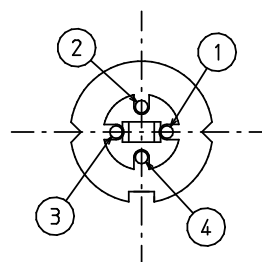
- Optical sensor / Optical encoder
- Optical Coherent Tomography (OCT)
- Optical measurement
- Substitute for high power LED



(Unit : mm)

PIN CONFIGURATION

No.	FUNCTION
1	SLD Cathode
2	PD Anode
3	SLD Anode
4	PD Cathode (case)



ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Ratings	Unit
SLD Reverse Voltage	V_R	2.0	V
Optical Output Power	P_O	6	mW
SLD Forward Current	I_F	120	mA
PD Reverse Voltage	V_{RD}	15	V
Operating Case Temperature	T_C	-20 to 70	°C
Storage Temperature ^{*1}	T_{stg}	-40 to 80	°C

*Excess over the absolute maximum ratings may cause device failure.

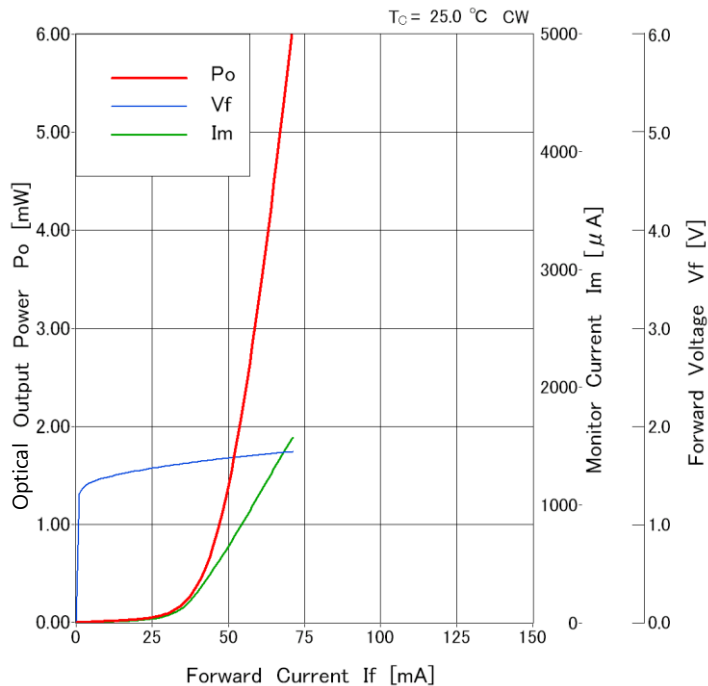
*1 No condensation

OPTICAL AND ELECTRICAL CHARACTERISTICS $(T_C = 25^\circ\text{C})$

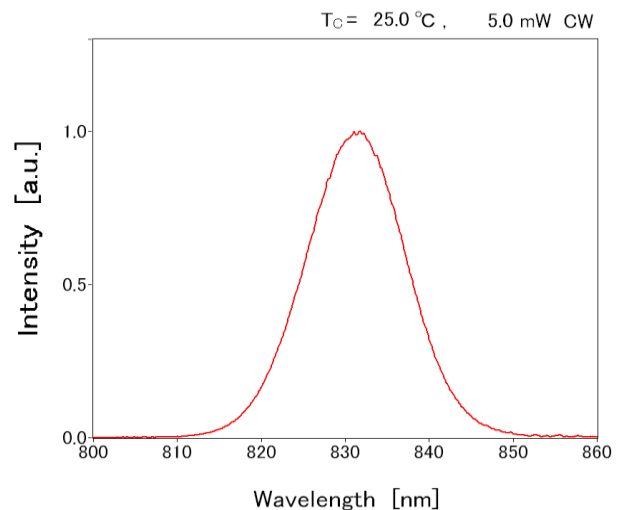
Item	Symbol	Test Condition	Min.	Typ.	Max.	Unit
SLD Forward Current	I_F	$P_O = 5 \text{ mW}$	—	70	100	mA
SLD Forward Voltage	V_F	$P_O = 5 \text{ mW}$	—	2.0	2.5	V
Center Wavelength	λ_C	$P_O = 5 \text{ mW}$	810	830	850	nm
Spectral Bandwidth	$\Delta\lambda$	$P_O = 5 \text{ mW}, -3 \text{ dB}$	10	15	—	nm
Spectral Modulation	M_d	$P_O = 5 \text{ mW}$	—	2	10	%
PD Monitor Current	I_m	$P_O = 5 \text{ mW}, V_{RD} = 5 \text{ V}$	0.2	1.5	2.2	mA
Parallel Beam Divergence	$\theta_{//}$	$P_O = 5 \text{ mW}$	—	15	—	deg.
Perpendicular Beam Divergence	$\theta_{\perp}$	$P_O = 5 \text{ mW}$	—	45	—	deg.

TYPICAL CHARACTERISTICS

Output Power/Forward Voltage/Monitor Current



Emission Spectrum





CAUTION : Handle the fiber of the enclosed device(s) with extreme care ; glass fiber is subject to breakage if mishandled and permanent damage to the device may result. Do not pull the device by the fiber or protective sleeve.
Do not coil the fiber into a loop of than 30 mm in radius.

SEMICONDUCTOR LASER

AVOID EXPOSURE
Invisible laser radiation is emitted from this aperture

DANGER

INVISIBLE LASER RADIATION
AVOID EYE OR SKIN EXPOSURE TO
DIRECT OR SCATTERED RADIATION

OUTPUT POWER 500mW
WAVELENGTH 0.80 to 1.80 μm
CLASS IIIb LASER PRODUCT

Caution - use of controls or adjustments or performance of procedures other than those specified herein may result in hazardous radiation exposure.
This Product Complies with 21 CFR 1040.10 and 1040.11
Manufactured Anritsu Corp. 5-1-1 Onna, Atsugi-shi, Kanagawa, Japan

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Contact URL

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Please read "Notes on Handling Optical Devices" before use.

<https://www.anritsu.com/sensing-devices/guide/optdevices-handling>



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